

Influence of Irradiation-Induced Defects on Anion Transport in Epitaxial Cr₂O₃

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Stability and degradation of structural materials within corrosive nuclear reactor environments are largely rate-limited by atomic transport mechanisms through protective oxide films. However, elevated temperatures and irradiation-induced defects interact and contribute to accelerated transport phenomena. In this study, anion transport is studied in a model passive oxide (Cr₂O₃) under irradiation using isotopic tracers and atom probe tomography (APT).

Isotopically labeled chromia (Cr₂O₃) films were deposited by molecular beam epitaxy (MBE). These films included an embedded ¹⁸O-rich tracer layer (10 nm thick, Figure 1a) to monitor atomic interdiffusion. Samples were divided and portions were subjected to 400 keV Ar²⁺ irradiation. Portions of the films were irradiated to 0.66 or 2 displacements per atom (dpa) at room temperature (RT), 300°C, or 500°C over time periods of 20 min – 2.5 hrs. 3D APT was then used to capture the elemental and O-isotopic redistribution within the film before and after irradiation. The ¹⁸O tracer distribution was quantified using the ¹⁸O isotopic fraction (*f*_{18O}), defined as $f_{18O} = N_{18O1+} / (N_{18O1+} + N_{16O1+})$ where *N*_{18O1+} and *N*_{16O1+} denote the measured counts of ¹⁸O¹⁺ and ¹⁶O¹⁺. *f*_{18O} profiles were used to calculate diffusion coefficients using Fick's second law and numerical methods.¹ Complementary scanning transmission electron microscopy (STEM) was conducted to study the microstructural evolution.

Representative microstructural characterization of the as-grown Cr₂O₃ is provided in Figure 1b and 1c. High angle annular dark field (HAADF) STEM shows a uniform Cr₂O₃ layer with no structural inhomogeneities at the buried ¹⁸O layer. Likewise, a representative APT reconstruction demonstrates a defined ¹⁸O layer embedded within natural abundance Cr₂O₃ layers. Quantitative *f*_{18O} profiles are provided in Figure 2 where the isotopic tracer layer broadens under irradiation compared to the as-grown deposition. Preliminary calculated diffusion coefficients for the 1 dpa specimens are 1.18×10^{-22} and 7.64×10^{-22} m²/s at RT and 500°C, respectively; approximately ten orders of magnitude higher than predicted by thermal diffusion alone. These values are consistent with chemical rate theory modeling conducted using defect formation and migration energies under irradiation of vacancies and interstitial defects.

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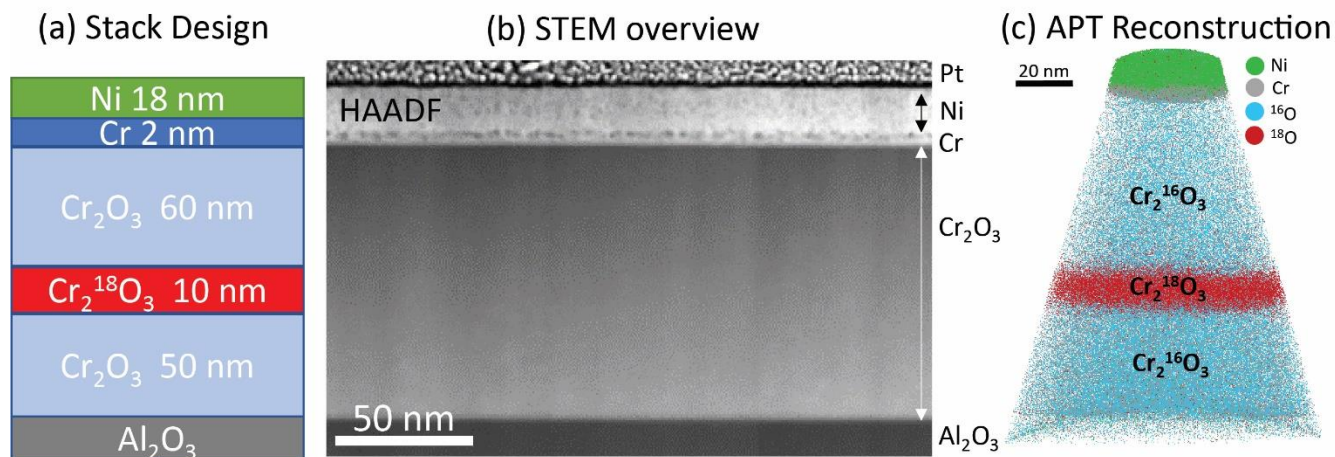


Figure 1. Figure 1. (a) Stack design showing embedded tracer layer ($\text{Cr}_2^{18}\text{O}_3$). (b) STEM-HAADF overview showing retention of caps, consistency of Cr_2O_3 layer on Al_2O_3 substrate (c) representative APT reconstruction of sample with embedded tracer layer (red).

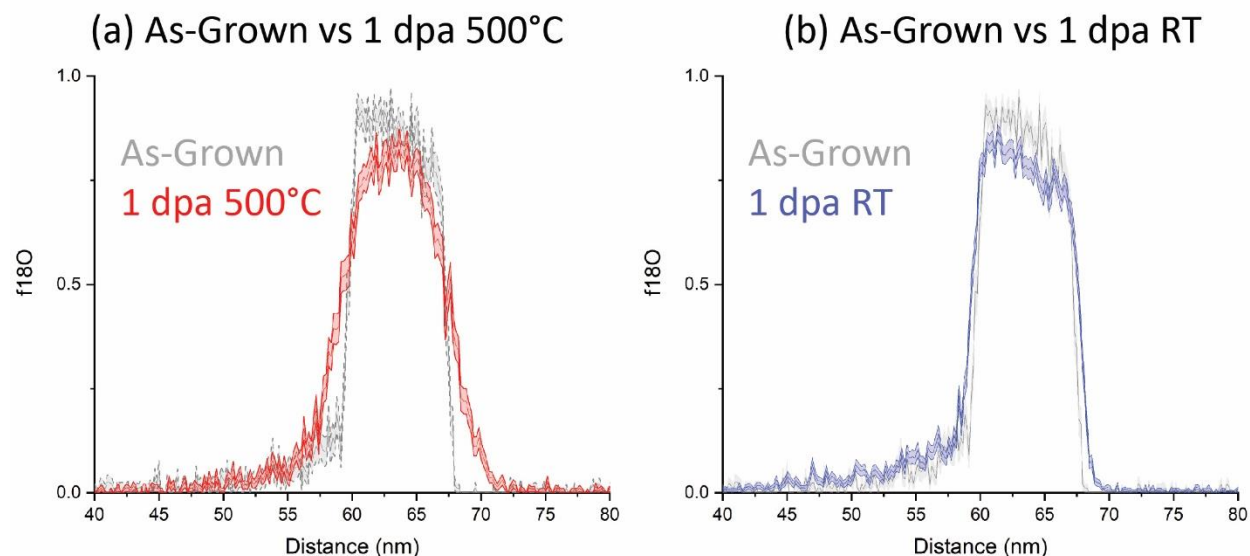


Figure 2. Figure 2. Fractional ^{18}O ($f_{18\text{O}}$) profiles of as-grown vs 400 keV Ar^{2+} irradiated specimens to 0.66 dpa at (a) 500°C and (b) RT. Profiles show broadening of $f_{18\text{O}}$ profiles as compared to the as-grown specimen, with more transport in the 500°C sample.

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